SKiM 180GD176D

SKiM® 4

IGBT Modules

SKiM 180GD176D

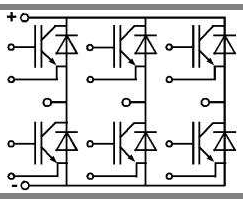
Target Data

Features

- Homogeneous Si
- Trench = Trenchgate Technology
- Low inductance case
- Isolated by Al_2O_3 DCB (Direct Copper Bonded) ceramic plate
- Pressure contact technology for thermal contacts
- V_{CEsat} with positive temperature coefficient
- High short circuit capability, self limiting to 6x I_C
- Integrated temperature sensor
- Spring contact system to attach driver PCB to the auxiliary terminals

Typical Applications

- AC inverter drives mains 575 - 750 V AC
- public transport (auxiliary syst.)



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Absolute Maximum Ratings		T_c = 25 °C, unless otherwise specified	
Symbol	**Conditions**	**Values**	**Units**
IGBT			
V_{CES}		1700	V
I_C	T_s = 25 (70) °C	180 (130)	A
I_{CM}	T_s = 25 (70) °C, t_p = 1 ms	360 (260)	A
V_{GES}		± 20	V
T_j (T_{stg})		- 40 ... +150 °C (125)	°C
T_{cop}	max. case operating temperature	125	°C
V_{isol}	AC, 1 min.	3300	V
Inverse diode			
I_F	T_s = 25 (70) °C	140 (100)	A
I_{FM} = - I_{CM}	T_s = 25 (70) °C, t_p = 1 ms	360 (260)	A
I_{FSM}	t_p = 10 ms; sin.; T_j = 150 °C	1450	A

Characteristics		T_c = 25 °C, unless otherwise specified			
Symbol	**Conditions**	**min.**	**typ.**	**max.**	**Units**
IGBT					
$V_{GE(th)}$	V_{GE} = V_{CE}; I_C = 8 mA	5,15	5,8	6,45	V
I_{CES}	V_{GE} = 0; V_{CE} = V_{CES}; T_j = 25 °C			0,3	mA
V_{CEO}	T_j = 25 (125) °C		1 (0,9)	1,2 (1,1)	V
r_{CE}	T_j = 25 () °C		5 (7,5)	6,3	mΩ
V_{CEsat}	I_C = 200 A; V_{GE} = 15 V, T_j = 25 (125) °C on chip level		2 (2,4)	2,45	V
C_{ies}	V_{GE} = 0; V_{CE} = 25 V; f = 1 MHz				nF
C_{oes}	V_{GE} = 0; V_{CE} = 25 V; f = 1 MHz				nF
C_{res}	V_{GE} = 0; V_{CE} = 25 V; f = 1 MHz				nF
L_{CE}					nH
$R_{CC'+EE'}$	resistance, terminal-chip T_c= 25 °C		1,1		mΩ
$t_{d(on)}$	V_{CC} = 1200 V				ns
t_r	I_C = 200 A				ns
$t_{d(off)}$	R_{Gon} = R_{Goff} = Ω				ns
t_f	T_j = 125 °C				ns
E_{on} (E_{off})	V_{GE} ± 15 V		120 (80)		mJ
E_{on} (E_{off})	with SKHI 64; T_j = 125 °C V_{CC} = 1200 V; I_C = 200 A				mJ
Inverse diode					
V_F = V_{EC}	I_F = 200 A; V_{GE} = 0 V; T_j = 25 (125) °C				V
V_{TO}	T_j = 25 (125) °C				V
r_T	T_j = 25 (125) °C				mΩ
I_{RRM}	I_F = 200 A; T_j = 125 °C				A
Q_{rr}	V_{GE} = 0 V di/dt = A/µs				µC
E_{rr}	R_{Gon} = R_{Goff} =				mJ
Thermal characteristics					
$R_{th(j-s)}$	per IGBT			0,25	K/W
$R_{th(j-s)}$	per FWD			0,45	K/W
Temperature Sensor					
R_{TS}	T = 25 (100) °C		1 (1,67)		kΩ
tolerance	T = 25 (100) °C		3 (2)		%
Mechanical data					
M_1	to heatsink (M5)	2		3	Nm
M_2	for terminals (M6)	4		5	Nm
w				310	g

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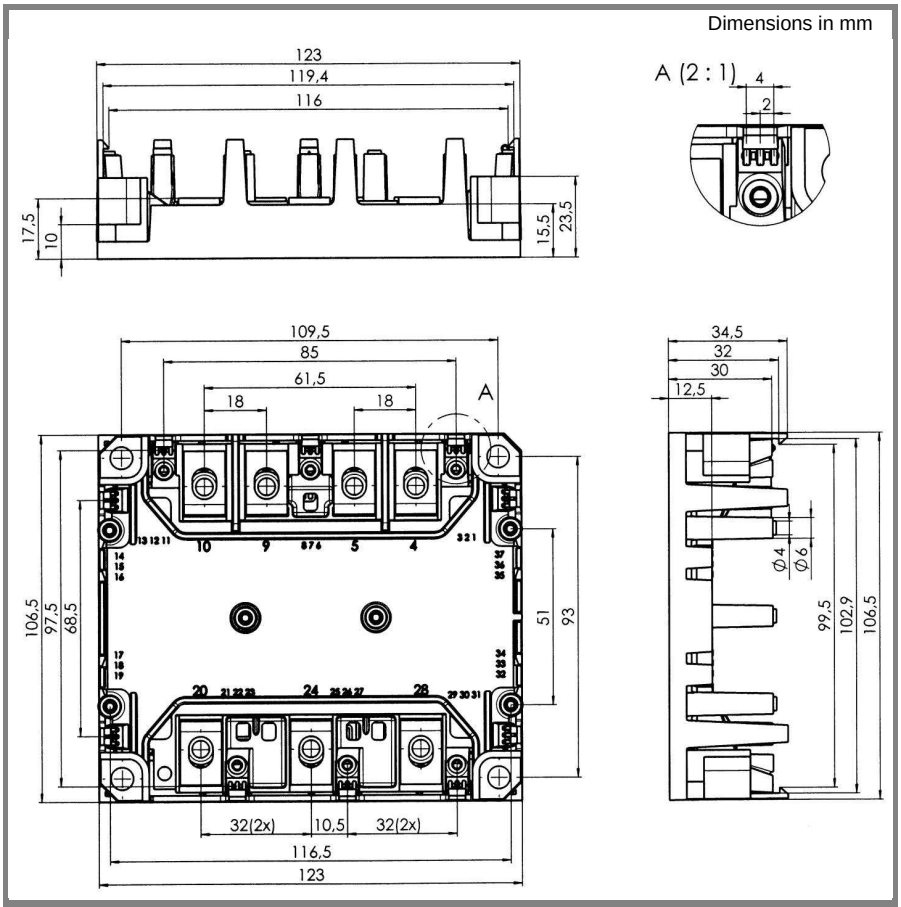
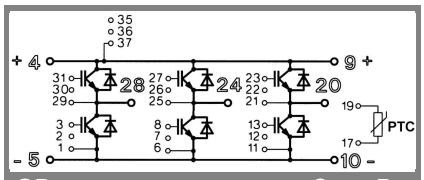


Case D



GD Case D

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

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